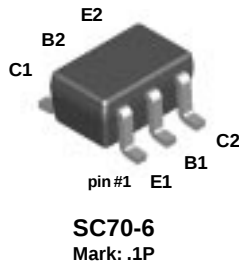
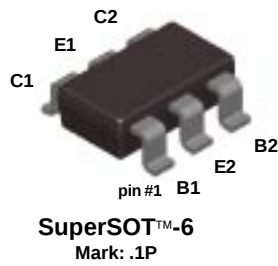


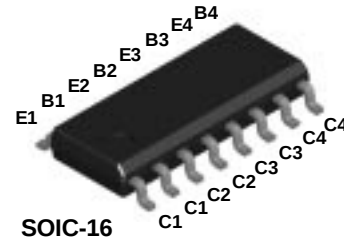
FFB2222A



FMB2222A



MMPQ2222A



NPN Multi-Chip General Purpose Amplifier

This device is for use as a medium power amplifier and switch requiring collector currents up to 500 mA. Sourced from Process 19.

Absolute Maximum Ratings*

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	40	V
V_{CBO}	Collector-Base Voltage	75	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I_C	Collector Current - Continuous	500	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Characteristic	Max			Units
		FFB2222A	FMB2222A	MMPQ2222A	
P_D	Total Device Dissipation Derate above 25°C	300	700	1,000	mW
		2.4	5.6	8.0	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient Effective 4 Die Each Die	415	180	125	$^\circ\text{C/W}$
				125	$^\circ\text{C/W}$
				240	$^\circ\text{C/W}$

NPN Multi-Chip General Purpose Amplifier

(continued)

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10\text{ mA}, I_B = 0$	40			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10\text{ }\mu\text{A}, I_E = 0$	75			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\text{ }\mu\text{A}, I_C = 0$	6.0			V
I_{CEX}	Collector Cutoff Current	$V_{CE} = 60\text{ V}, V_{EB(OFF)} = 3.0\text{ V}$			10	nA
I_{CBO}	Collector Cutoff Current	$V_{CB} = 60\text{ V}, I_E = 0$ $V_{CB} = 60\text{ V}, I_E = 0, T_A = 125^\circ\text{C}$			0.01 10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 3.0\text{ V}, I_C = 0$			10	nA
I_{BL}	Base Cutoff Current	$V_{CE} = 60\text{ V}, V_{EB(OFF)} = 3.0\text{ V}$			20	nA

ON CHARACTERISTICS

h_{FE}	DC Current Gain	$I_C = 0.1\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 1.0\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 10\text{ V}, T_A = -55^\circ\text{C}$ $I_C = 150\text{ mA}, V_{CE} = 10\text{ V}^*$ $I_C = 150\text{ mA}, V_{CE} = 1.0\text{ V}^*$ $I_C = 500\text{ mA}, V_{CE} = 10\text{ V}^*$	35 50 75 35 100 50 40		300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage*	$I_C = 150\text{ mA}, I_B = 15\text{ mA}$ $I_C = 500\text{ mA}, I_B = 50\text{ mA}$			0.3 1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage*	$I_C = 150\text{ mA}, I_B = 1.0\text{ mA}$ $I_C = 500\text{ mA}, I_B = 50\text{ mA}$	0.6		1.2 2.0	V

SMALL SIGNAL CHARACTERISTICS

f_T	Current Gain - Bandwidth Product	$I_C = 20\text{ mA}, V_{CE} = 20\text{ V},$ $f = 100\text{ MHz}$		300		MHz
C_{obo}	Output Capacitance	$V_{CB} = 10\text{ V}, I_E = 0, f = 100\text{ kHz}$		4.0		pF
C_{ibo}	Input Capacitance	$V_{EB} = 0.5\text{ V}, I_C = 0, f = 100\text{ kHz}$		20		pF
NF	Noise Figure	$I_C = 100\text{ }\mu\text{A}, V_{CE} = 10\text{ V},$ $R_S = 1.0\text{ k}\Omega, f = 1.0\text{ kHz}$		2.0		dB

SWITCHING CHARACTERISTICS

t_d	Delay Time	$V_{CC} = 30\text{ V}, V_{BE(OFF)} = 0.5\text{ V},$		8		ns
t_r	Rise Time	$I_C = 150\text{ mA}, I_{B1} = 15\text{ mA}$		20		ns
t_s	Storage Time	$V_{CC} = 30\text{ V}, I_C = 150\text{ mA},$		180		ns
t_f	Fall Time	$I_{B1} = I_{B2} = 15\text{ mA}$		40		ns

*Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$

FFB2222A / FMB2222A / MMPQ2222A

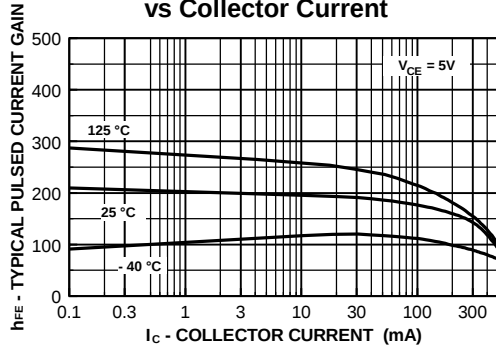
NPN Multi-Chip General Purpose Amplifier

(continued)

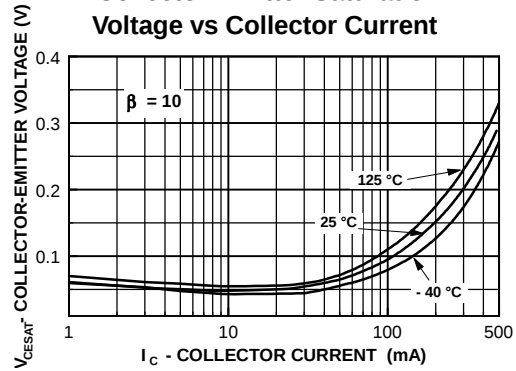
FFB2222A / FMB2222A / MMPQ2222A

Typical Characteristics

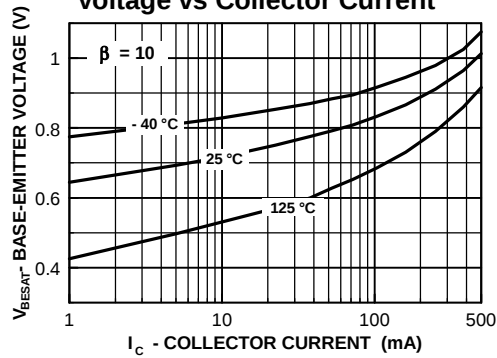
Typical Pulsed Current Gain
vs Collector Current



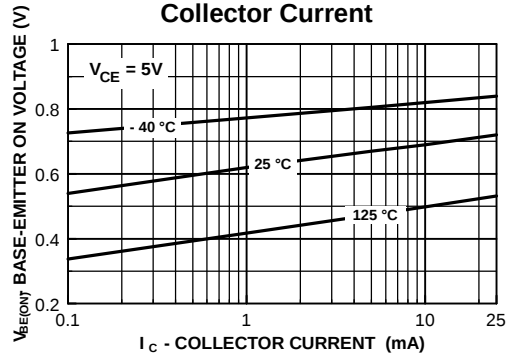
Collector-Emitter Saturation
Voltage vs Collector Current



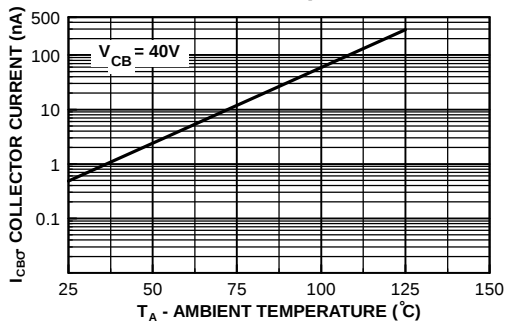
Base-Emitter Saturation
Voltage vs Collector Current



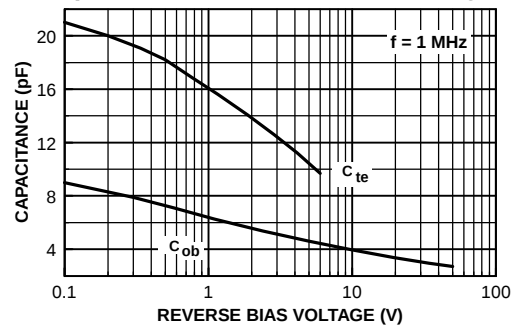
Base-Emitter ON Voltage vs
Collector Current



Collector-Cutoff Current
vs Ambient Temperature

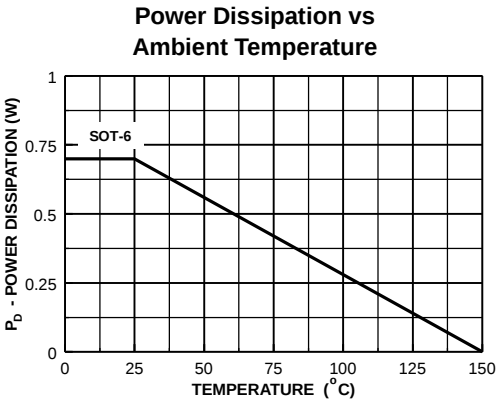
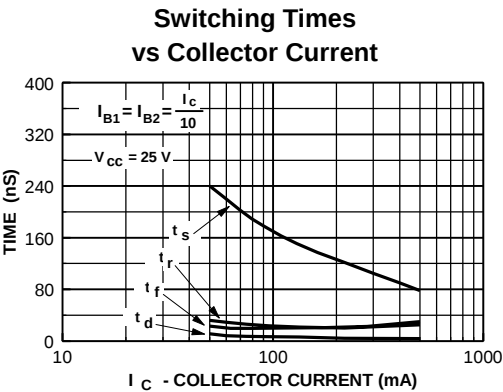
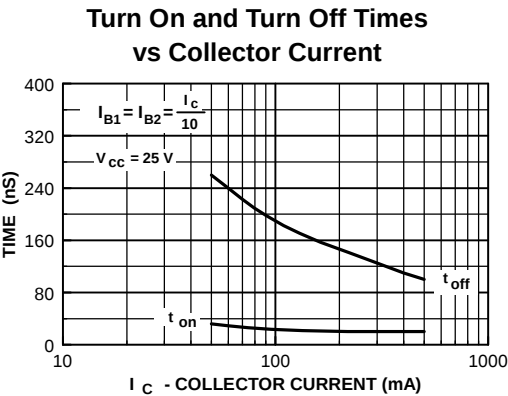


Emitter Transition and Output
Capacitance vs Reverse Bias Voltage



NPN Multi-Chip General Purpose Amplifier
(continued)

Typical Characteristics (continued)



FFB2222A / FMB2222A / MMPQ2222A

Test Circuits

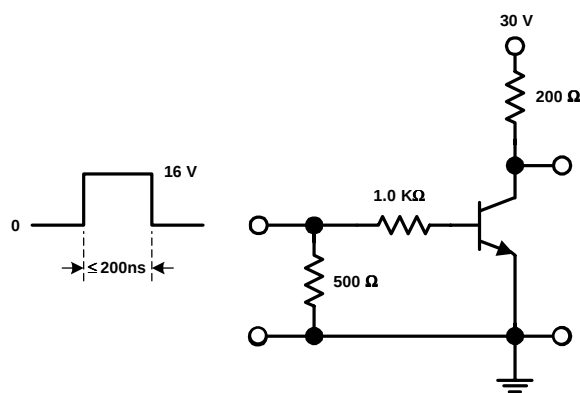


FIGURE 1: Saturated Turn-On Switching Time

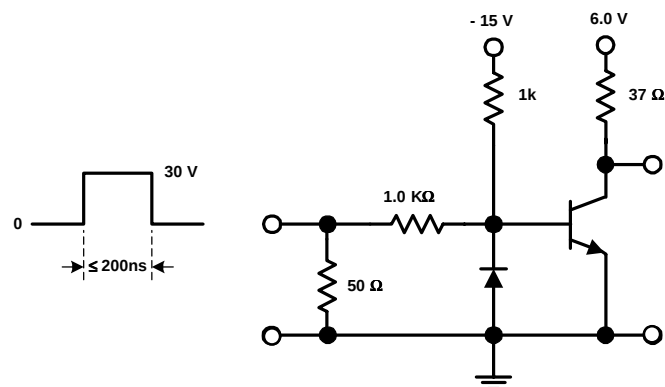


FIGURE 2: Saturated Turn-Off Switching Time